SOT223 PNP SILICON PLANAR SWITCHING TRANSISTOR

FZT4403

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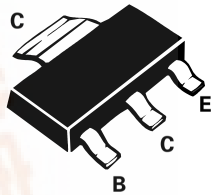
PARTMARKING DETAIL – FZT4403



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-600	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	1.5	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		V	I_C=-0.1mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	I_C=-1mA
Emitter Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-0.1mA
Base Cut-off Current	I_{BEX}		-0.1	µA	V_{CE}=-35V, $V_{EB(OFF)}$=-0.4V
Collector-Emitter Cut-off Current	I_{CEX}		-0.1	µA	V_{CE}=-35V, $V_{EB(OFF)}$=-0.4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.4 -0.75	V V	I_C=-150mA, I_B=-15mA* I_C=-500mA, I_B=-50mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.75	-0.95 -1.3	V V	I_C=-150mA, I_B=-15mA* I_C=-500mA, I_B=-50mA*
Static Forward Current Transfer Ratio	h_{FE}	30 60 100 100 20	 300		I_C=-0.1mA, V_{CE}=-1V I_C=-1mA, V_{CE}=-1V I_C=-10mA, V_{CE}=-1V I_C=-150mA, V_{CE}=-2V* I_C=-500mA, V_{CE}=-2V*
Transition Frequency	f_T	200		MHz	I_C=-50mA, V_{CE}=-5V f=100MHz
Output Capacitance	C_{obo}		8.5	pF	V_{CB}=-10V, f=100KHz I_E=0
Input Capacitance	C_{ibo}		30	pF	I_C=0, f=100kHZ

*Measured under pulsed conditions. Pulse width=300µs.